

(19) World Intellectual Property
Organization
International Bureau



WIPO | PCT



(10) International Publication Number
WO 2025/151845 A8

(43) International Publication Date
17 July 2025 (17.07.2025)

- (51) **International Patent Classification:**
H01L 21/027 (2006.01) *H01L 21/32* (2006.01)
- (21) **International Application Number:**
PCT/US2025/011322
- (22) **International Filing Date:**
12 January 2025 (12.01.2025)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
63/620,403 12 January 2024 (12.01.2024) US
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- (81) **Designated States (unless otherwise indicated, for every kind of national protection available):** AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH,

TJ, TM, TN, TR, TT, TZ, UA, UG, US, UY, UZ, VC, VN, WS, ZA, ZM, ZW.

- (84) **Designated States (unless otherwise indicated, for every kind of regional protection available):** ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— of inventorship (Rule 4.17(iv))

Published:

— with international search report (Art. 21(3))

(48) Date of publication of this corrected version:

09 July 2026 (09.07.2026)

(15) Information about Correction:

see Notice of 09 July 2026 (09.07.2026)

(54) **Title:** METHOD FOR FABRICATION OF FINE-FEATURED ETCH MASK USING DIRECT ATOMIC LAYER PROCESSING

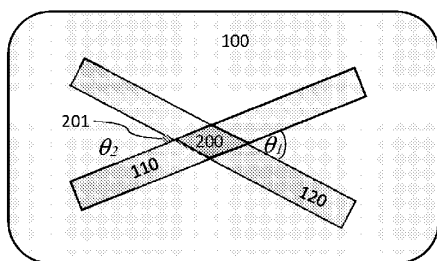


FIG. 4A

(57) **Abstract:** The disclosure relates to systems and methods for forming etch masks using direct atomic layer processing. Specifically, the disclosure relates to methods of forming etch masks having fine features at the substrate level, using microreactor direct atomic layer processing (μ DALP).